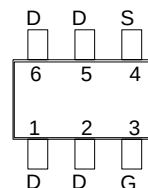
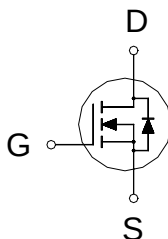


PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30	27m Ω	7A



1. GATE
2. DRAIN
3. SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25\text{ }^\circ\text{C}$	I_D	7	A
	$T_C = 100\text{ }^\circ\text{C}$		5	
Pulsed Drain Current ¹		I_{DM}	20	
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	1.6	W
	$T_C = 100\text{ }^\circ\text{C}$		1.2	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	$^\circ\text{C}$
Lead Temperature ($1/16"$ from case for 10 sec.)		T_L	275	

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		30	$^\circ\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		78	

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$

ELECTRICAL CHARACTERISTICS ($T_C = 25\text{ }^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.5	3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24V, V_{GS} = 0V$			1	μA
		$V_{DS} = 20V, V_{GS} = 0V, T_J = 125\text{ }^{\circ}C$			10	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 5V, V_{GS} = 10V$	20			A
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 5A$		32	40	mΩ
		$V_{GS} = 10V, I_D = 7A$		23	27	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 7A$		14.4		S

DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 10V, f = 1MHz		680		pF
Output Capacitance	C _{oss}			140		
Reverse Transfer Capacitance	C _{rss}			70		
Total Gate Charge ²	Q _g	V _{DS} = 15V, V _{GS} = 10V, I _D = 7A		10	15	nC
Gate-Source Charge ²	Q _{gs}			1.7		
Gate-Drain Charge ²	Q _{gd}			2.1		
Turn-On Delay Time ²	t _{d(on)}	V _{DS} = 10V, I _D ≅ 1A, V _{GS} = 10V, R _{GEN} = 6Ω		8.0		nS
Rise Time ²	t _r			4.0		
Turn-Off Delay Time ²	t _{d(off)}			22.0		
Fall Time ²	t _f			5.0		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _c = 25 °C)						
Continuous Current	I _S				3	A
Forward Voltage ¹	V _{SD}	I _F = 1A, V _{GS} = 0V			1.1	V

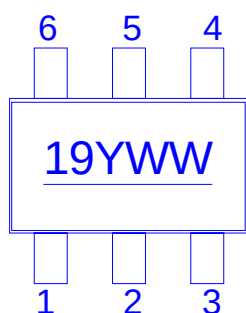
¹Pulse test : Pulse Width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

REMARK: THE PRODUCT MARKED WITH “19YWW”, DATE CODE or LOT #

Orders for parts with Lead-Free plating can be placed using the PXXXXXXG parts name



Marking Description:

1 - N MOSFET

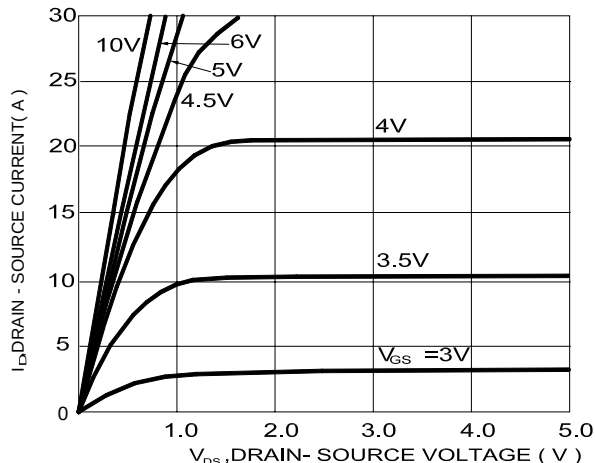
9 - Serial Number

Y - Year

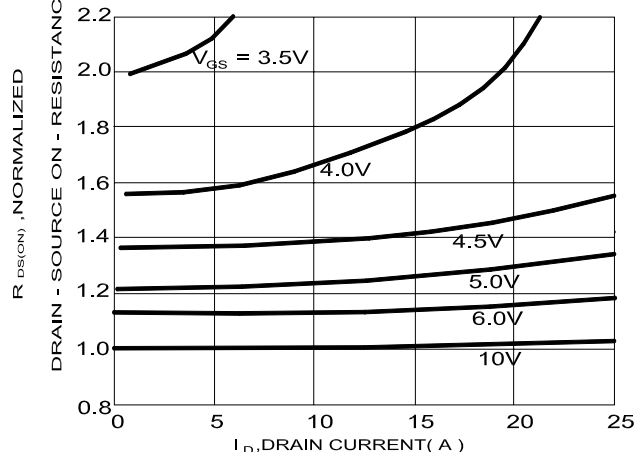
W - Week

TYPICAL CHARACTERISTICS

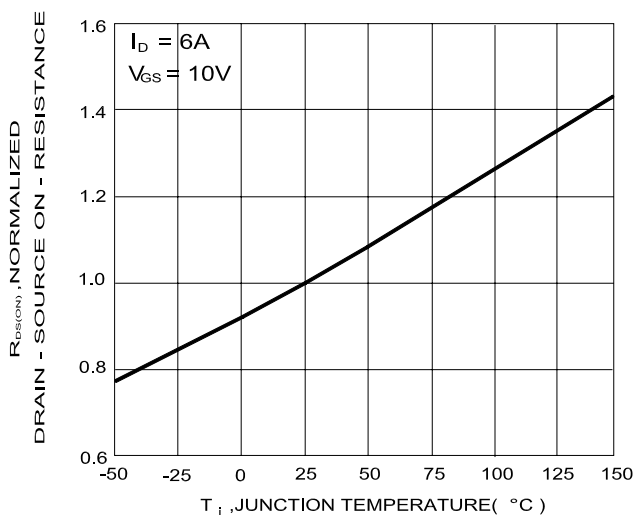
ON-REGION CHARACTERISTIC



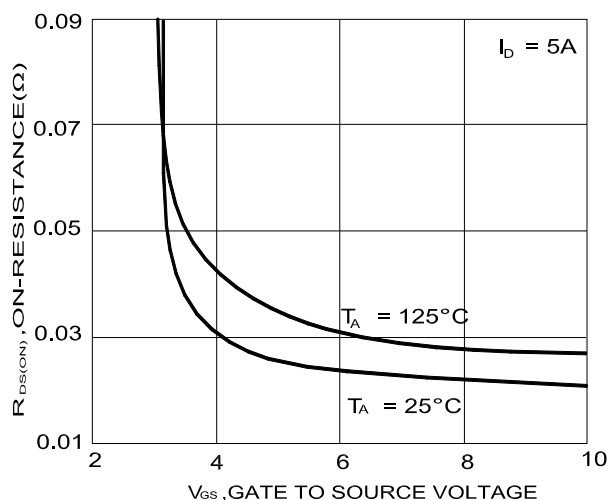
ON- RESISTANCE VARIATION WITH DRAIN CURRENT AND GATE VOLTAGE



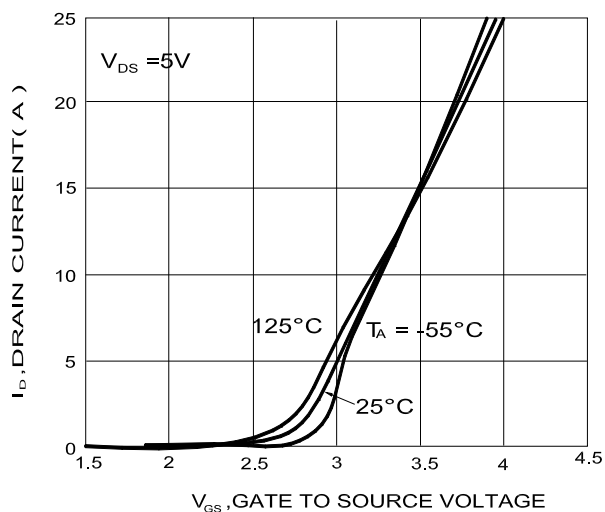
ON- RESISTANCE VARIATION WITH TEMPERATURE



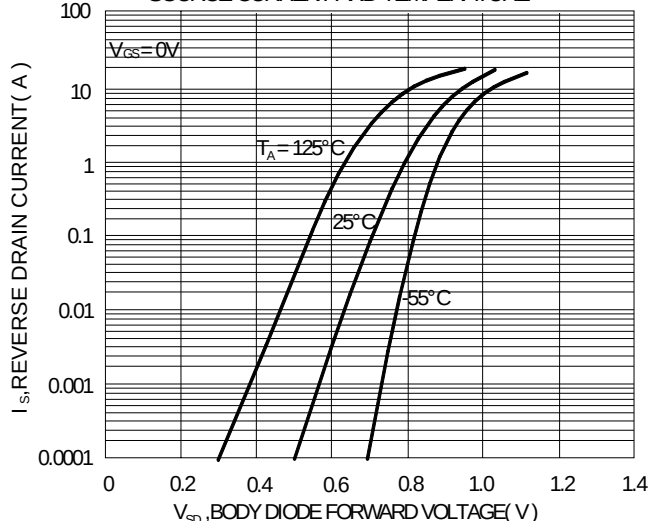
ON-RESISTANCE VARIATION WITH GATE-TO-SOURCE VOLTAGE



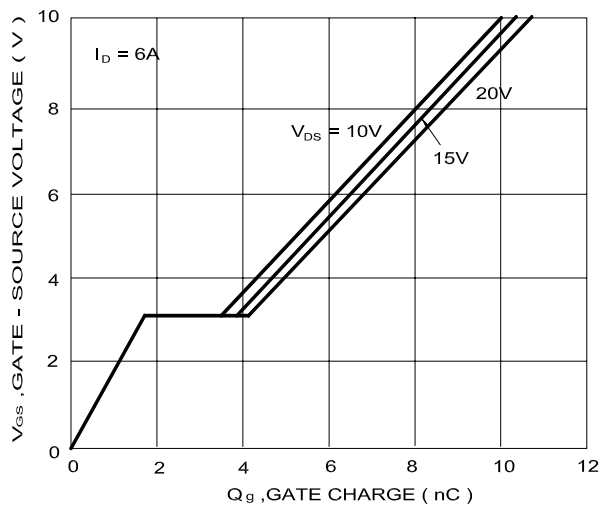
TRANSFER CHARACTERISTICS



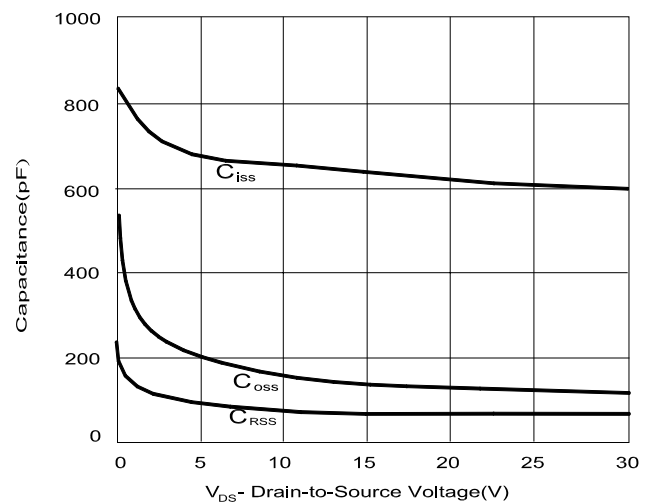
BODY DIODE FORWARD VOLTAGE VARIATION WITH SOURCE CURRENT AND TEMPERATURE



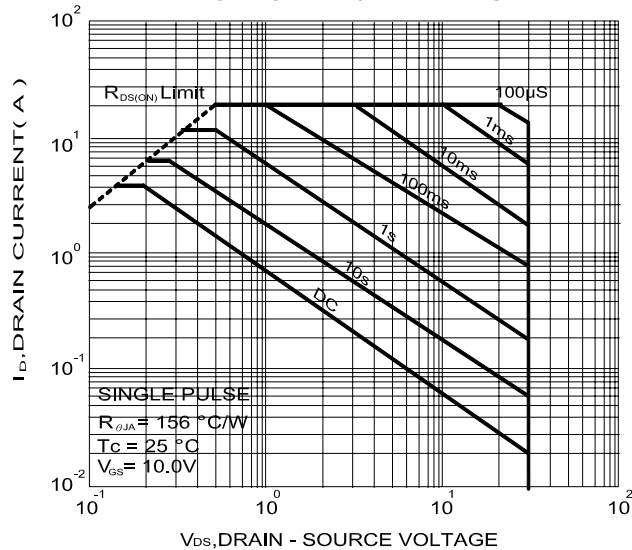
GATE CHARGE CHARACTERISTICS



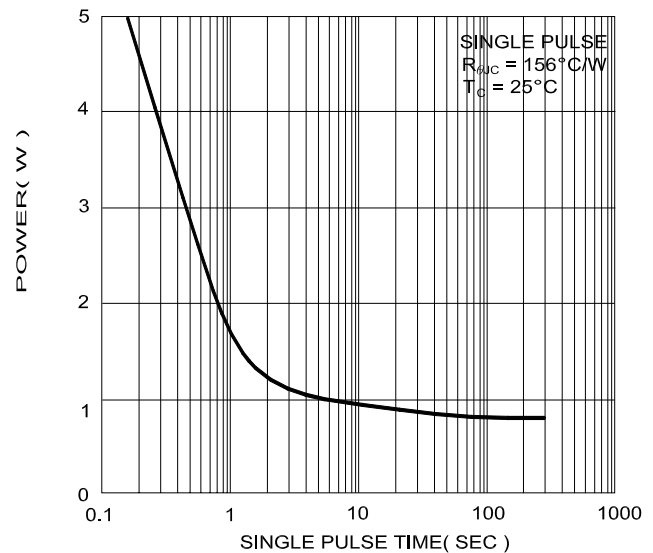
Capacitance Characteristics



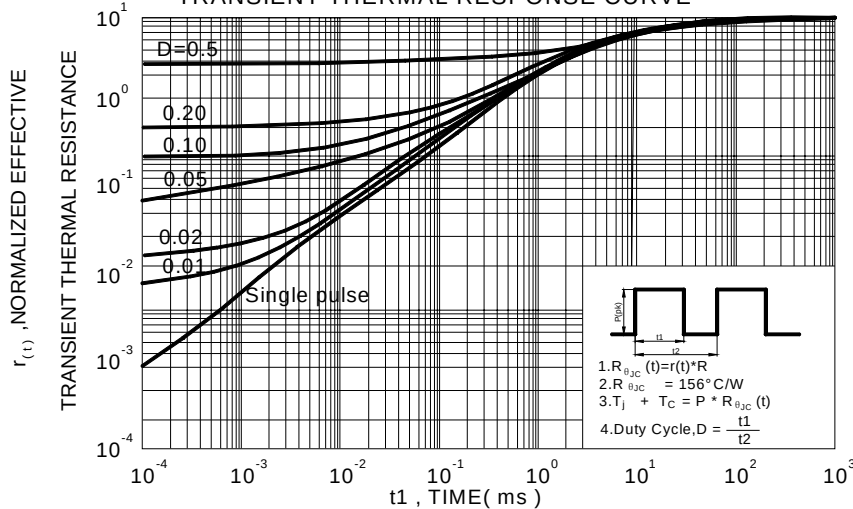
MAXIMUM SAFE OPERATING AREA



SINGLEPULSE MAXIMUM POWER DISSIPATION



TRANSIENT THERMAL RESPONSE CURVE



TSOP- 6 MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A		0.95		H	0.08	0.13	0.2
B	2.5	2.8	3.1	I	0.3		0.6
C	1.5	1.6	1.7	J			
D	2.7	2.9	3.1	K			
E	0.7		1.2	L			
F	0		0.15	M			
G	0.3	0.4	0.5	N			

